



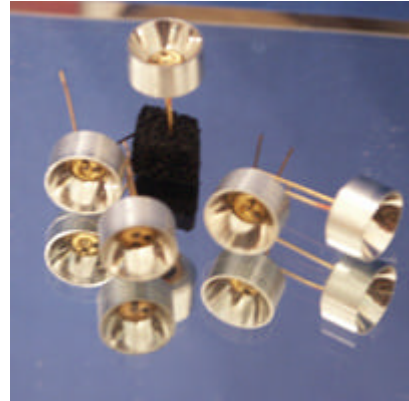
LIGHT EMITTING DIODES 1.6÷4.6 μm

Model LED34-PR 3.4 μm 24 μW

•Light Emitting Diodes **LED34-PR** are designed for emitting at a spectral range around 3400 nm. Heterostructures (HS) are grown on InAs substrates. The output emission can be modulated by current flowing in a forward direction.

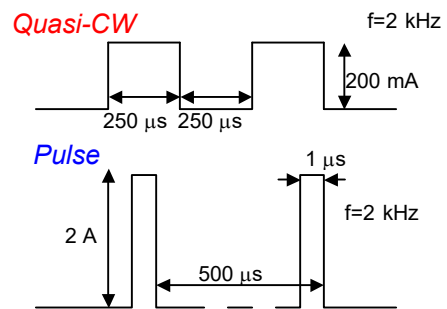
•Light Emitting Diodes **LED34-PR** are developed for using in optical gas sensors and medical diagnostics. They have stable output power and lifetime more than 10000 hours.

•Related products: **LED34-PR** can be used in optical pair with our photodiodes **PD36**. Our standard **LED Driver** provides power supply of **LED34-PR** in two recommended here regimes (Quasi-CW and Pulsed).



| Parameters | Min | Typ | Max |
|---------------------------------|--------------------------------|------|------|
| Wavelength, μm | 3.30 | 3.40 | 3.50 |
| FWHM, μm | 0.60 | 0.70 | 0.80 |
| Optical Power, μW | | | |
| Quasi-CW @ 200 mA | 20 | 24 | 28 |
| Pulsed@1A | 320 | 400 | 480 |
| Switching Time, ns | 10 | 30 | 50 |
| Operating Temperature Range, °C | -240÷+50 | | |
| Emitting Area, μm | 300x300 | | |
| Soldering temperature | 260 °C | | |
| Package | TO-18 with Parabolic Reflector | | |

Recommended regimes of operation



Package TO-18 with Reflector

